

Armin Dadgar

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259
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ext. citations

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L-index

#	Paper	IF	Citations
238	Metalorganic Chemical Vapor Phase Epitaxy of Crack-Free GaN on Si (111) Exceeding 1 μm in Thickness. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, L1183-L1185	1.4	281
237	GaN-based optoelectronics on silicon substrates. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002 , 93, 77-84	3.1	240
236	Template-assisted large-scale ordered arrays of ZnO pillars for optical and piezoelectric applications. <i>Small</i> , 2006 , 2, 561-8	11	194
235	Thick, crack-free blue light-emitting diodes on Si(111) using low-temperature AlN interlayers and in situ SixNy masking. <i>Applied Physics Letters</i> , 2002 , 80, 3670-3672	3.4	169
234	GaN-Based Devices on Si. <i>Physica Status Solidi A</i> , 2002 , 194, 361-375		146
233	Arrays of vertically aligned and hexagonally arranged ZnO nanowires: a new template-directed approach. <i>Nanotechnology</i> , 2005 , 16, 913-917	3.4	138
232	High Si and Ge n-type doping of GaN doping - Limits and impact on stress. <i>Applied Physics Letters</i> , 2012 , 100, 122104	3.4	127
231	MOVPE growth of GaN on Si(1 1 1) substrates. <i>Journal of Crystal Growth</i> , 2003 , 248, 556-562	1.6	117
230	High-sheet-charge-barrier-density AlInN/GaN field-effect transistors on Si(111). <i>Applied Physics Letters</i> , 2004 , 85, 5400-5402	3.4	116
229	Band gap renormalization and Burstein-Moss effect in silicon- and germanium-doped wurtzite GaN up to 1020 cm \bar{B} . <i>Physical Review B</i> , 2014 , 90,	3.3	112
228	Metal-organic vapor phase epitaxy and properties of AlInN in the whole compositional range. <i>Applied Physics Letters</i> , 2007 , 90, 022105	3.4	111
227	GaN-based epitaxy on silicon: stress measurements. <i>Physica Status Solidi A</i> , 2003 , 200, 26-35		111
226	Gallium nitride vertical power devices on foreign substrates: a review and outlook. <i>Journal Physics D: Applied Physics</i> , 2018 , 51, 273001	3	109
225	Growth of blue GaN LED structures on 150-mm Si(1 1 1). <i>Journal of Crystal Growth</i> , 2006 , 297, 279-282	1.6	109
224	Efficient stress relief in GaN heteroepitaxy on Si(111) using low-temperature AlN interlayers. <i>Journal of Crystal Growth</i> , 2003 , 248, 563-567	1.6	108
223	Recording of cell action potentials with AlGaN/GaN field-effect transistors. <i>Applied Physics Letters</i> , 2005 , 86, 033901	3.4	107
222	Epitaxy of GaN on silicon-impact of symmetry and surface reconstruction. <i>New Journal of Physics</i> , 2007 , 9, 389-389	2.9	106

221	The origin of stress reduction by low-temperature AlN interlayers. <i>Applied Physics Letters</i> , 2002 , 81, 2722-2724	3.4	106
220	Atomic arrangement at the AlN/Si (111) interface. <i>Applied Physics Letters</i> , 2003 , 83, 860-862	3.4	102
219	Metalorganic chemical vapor phase epitaxy of gallium-nitride on silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 1583-1606		101
218	Bright blue electroluminescence from an InGaN/GaN multiquantum-well diode on Si(111): Impact of an AlGaIn/GaN multilayer. <i>Applied Physics Letters</i> , 2001 , 78, 2211-2213	3.4	100
217	Dislocation annihilation by silicon delta-doping in GaN epitaxy on Si. <i>Applied Physics Letters</i> , 2002 , 81, 4712-4714	3.4	98
216	Well-ordered ZnO nanowire arrays on GaN substrate fabricated via nanosphere lithography. <i>Journal of Crystal Growth</i> , 2006 , 287, 34-38	1.6	97
215	Reduction of stress at the initial stages of GaN growth on Si(111). <i>Applied Physics Letters</i> , 2003 , 82, 28-30	3.4	94
214	Piezoelectric GaN sensor structures. <i>IEEE Electron Device Letters</i> , 2006 , 27, 309-312	4.4	93
213	Vapour-transport-deposition growth of ZnO nanostructures: switch between axial wires and axial belts by indium doping. <i>Nanotechnology</i> , 2006 , 17, S231-S239	3.4	89
212	Laser-interference lithography tailored for highly symmetrically arranged ZnO nanowire arrays. <i>Small</i> , 2007 , 3, 76-80	11	86
211	Local p-type conductivity in zinc oxide dual-doped with nitrogen and arsenic. <i>Applied Physics Letters</i> , 2005 , 87, 2621-2625	3.4	86
210	Fabrication, self-assembly, and properties of ultrathin AlN/GaN porous crystalline nanomembranes: tubes, spirals, and curved sheets. <i>ACS Nano</i> , 2009 , 3, 1663-8	16.7	82
209	MOVPE growth of GaN on Si substrates and strain. <i>Thin Solid Films</i> , 2007 , 515, 4356-4361	2.2	71
208	Transient thermal characterization of AlGaIn/GaN HEMTs grown on silicon. <i>IEEE Transactions on Electron Devices</i> , 2005 , 52, 1698-1705	2.9	69
207	Patterned growth of aligned ZnO nanowire arrays on sapphire and GaN layers. <i>Superlattices and Microstructures</i> , 2004 , 36, 95-105	2.8	67
206	MOVPE growth of high-quality AlN. <i>Journal of Crystal Growth</i> , 2006 , 297, 306-310	1.6	64
205	Sixteen years GaN on Si. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 1063-1068	1.3	63
204	Crack-Free, Highly Conducting GaN Layers on Si Substrates by Ge Doping. <i>Applied Physics Express</i> , 2011 , 4, 011001	2.4	63

203	High-Performance 500 V Quasi- and Fully-Vertical GaN-on-Si pn Diodes. <i>IEEE Electron Device Letters</i> , 2017 , 38, 248-251	4.4	61
202	Fabry-Perot effects in InGaN/GaN heterostructures on Si-substrate. <i>Journal of Applied Physics</i> , 2007 , 101, 033113	2.5	60
201	Two charge states of the CN acceptor in GaN: Evidence from photoluminescence. <i>Physical Review B</i> , 2018 , 98,	3.3	58
200	Dielectric function and optical properties of Al-rich AlInN alloys pseudomorphically grown on GaN. <i>Journal Physics D: Applied Physics</i> , 2010 , 43, 365102	3	54
199	P-channel InGaN-HFET structure based on polarization doping. <i>IEEE Electron Device Letters</i> , 2004 , 25, 450-452	4.4	54
198	Improving GaN-on-silicon properties for GaN device epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 1503-1508		51
197	A two-step metal organic vapor phase epitaxy growth method for high-quality ZnO on GaN/Al ₂ O ₃ (0001). <i>Journal of Crystal Growth</i> , 2004 , 267, 140-144	1.6	51
196	Thermal stability of metal organic vapor phase epitaxy grown AlInN. <i>Applied Physics Letters</i> , 2007 , 90, 221906	3.4	50
195	Self-assembly of ZnO nanowires and the spatial resolved characterization of their luminescence. <i>Nanotechnology</i> , 2004 , 15, 1401-1404	3.4	50
194	All metalorganic chemical vapor phase epitaxy of p/n-GaN tunnel junction for blue light emitting diode applications. <i>Applied Physics Letters</i> , 2017 , 110, 102104	3.4	48
193	Decoration effects as origin of dislocation-related charges in gallium nitride layers investigated by scanning surface potential microscopy. <i>Applied Physics Letters</i> , 2003 , 82, 2263-2265	3.4	46
192	Metalorganic chemical vapor phase deposition of ZnO with different O-precursors. <i>Journal of Crystal Growth</i> , 2003 , 248, 14-19	1.6	45
191	Crack-Free InGaN/GaN Light Emitters on Si(111). <i>Physica Status Solidi A</i> , 2001 , 188, 155-158		45
190	Influence of buffer layers on metalorganic vapor phase epitaxy grown GaN on Si(001). <i>Applied Physics Letters</i> , 2004 , 84, 4747-4749	3.4	43
189	Influence of exciton-phonon coupling and strain on the anisotropic optical response of wurtzite AlN around the band edge. <i>Physical Review B</i> , 2011 , 83,	3.3	41
188	Metalorganic vapor phase epitaxy grown InGaN/GaN light-emitting diodes on Si(001) substrate. <i>Applied Physics Letters</i> , 2006 , 88, 121114	3.4	40
187	In situ measurements of strains and stresses in GaN heteroepitaxy and its impact on growth temperature. <i>Journal of Crystal Growth</i> , 2004 , 272, 72-75	1.6	39
186	Bright, Crack-Free InGaN/GaN Light Emitters on Si(111). <i>Physica Status Solidi A</i> , 2002 , 192, 308-313		39

185	Homoepitaxial growth of ZnO by metalorganic vapor phase epitaxy in two-dimensional growth mode. <i>Journal of Crystal Growth</i> , 2007 , 308, 170-175	1.6	37
184	Ostwald ripening and flattening of epitaxial ZnO layers during in situ annealing in metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2004 , 85, 1496-1498	3.4	37
183	In situ monitoring of the stress evolution in growing group-III-nitride layers. <i>Journal of Crystal Growth</i> , 2005 , 275, 209-216	1.6	37
182	InGaN/GaN light-emitting diodes on Si(1 1 0) substrates grown by metalorganic vapour phase epitaxy. <i>Journal Physics D: Applied Physics</i> , 2009 , 42, 055107	3	35
181	Evolution of stress in GaN heteroepitaxy on AlN/Bi(111): From hydrostatic compressive to biaxial tensile. <i>Applied Physics Letters</i> , 2004 , 85, 3441-3443	3.4	35
180	High-current AlInN/GaN field effect transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005 , 202, 832-836	1.6	35
179	UNSTRAINED InAlN/GaN HEMT STRUCTURE. <i>International Journal of High Speed Electronics and Systems</i> , 2004 , 14, 785-790	0.5	34
178	InGaN/GaN light emitting diodes on nanoscale silicon on insulator. <i>Applied Physics Letters</i> , 2007 , 91, 231109	3.4	33
177	Reduction of on-resistance and current crowding in quasi-vertical GaN power diodes. <i>Applied Physics Letters</i> , 2017 , 111, 163506	3.4	32
176	Germanium – the superior dopant in n-type GaN. <i>Physica Status Solidi - Rapid Research Letters</i> , 2015 , 9, 716-721	2.5	32
175	Role of low-temperature AlGaIn interlayers in thick GaN on silicon by metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2012 , 111, 124505	2.5	32
174	Anisotropy of effective electron masses in highly doped nonpolar GaN. <i>Applied Physics Letters</i> , 2013 , 103, 232104	3.4	31
173	Optical and structural microanalysis of GaN grown on SiN submonolayers. <i>Journal of Applied Physics</i> , 2006 , 99, 123518	2.5	31
172	Two-dimensional electron gas based actuation of piezoelectric AlGaIn/GaN microelectromechanical resonators. <i>Applied Physics Letters</i> , 2008 , 93, 173504	3.4	30
171	Complex excitonic recombination kinetics in ZnO: Capture, relaxation, and recombination from steady state. <i>Applied Physics Letters</i> , 2007 , 90, 041917	3.4	29
170	Growth of single-domain GaN layers on Si(001) by metalorganic vapor-phase epitaxy. <i>Journal of Crystal Growth</i> , 2006 , 289, 485-488	1.6	29
169	Valence-band splitting and optical anisotropy of AlN. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 1679-1682	1.3	26
168	ZnO MOVPE growth: From local impurity incorporation towards p-type doping. <i>Superlattices and Microstructures</i> , 2005 , 38, 245-255	2.8	26

167	Analysis of point defects in AlN epilayers by cathodoluminescence spectroscopy. <i>Applied Physics Letters</i> , 2009 , 95, 032106	3.4	25
166	Ruthenium: A superior compensator of InP. <i>Applied Physics Letters</i> , 1998 , 73, 3878-3880	3.4	25
165	Direct evidence of single quantum dot emission from GaN islands formed at threading dislocations using nanoscale cathodoluminescence: A source of single photons in the ultraviolet. <i>Applied Physics Letters</i> , 2015 , 106, 252101	3.4	24
164	Properties of C-doped GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2017 , 254, 1600708	1.3	23
163	Wafer curvature in the nonlinear deformation range. <i>Physica Status Solidi A</i> , 2004 , 201, R75-R78		23
162	Metal Organic Vapor Phase Epitaxy of ZnO on GaN/Si(111) Using Tertiary-Butanol as O-Precursor. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, 7474-7477	1.4	23
161	Modulation spectroscopy of AlGaIn/GaN heterostructures: The influence of electron-hole interaction. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 447-458	1.6	22
160	Methodology for the investigation of threading dislocations as a source of vertical leakage in AlGaIn/GaN-HEMT heterostructures for power devices. <i>Journal of Applied Physics</i> , 2019 , 125, 095704	2.5	21
159	Semipolar single component GaN on planar high index Si(11h) substrates. <i>Applied Physics Letters</i> , 2010 , 97, 142102	3.4	21
158	Metal organic vapor phase epitaxy growth of single crystalline GaN on planar Si(211) substrates. <i>Applied Physics Letters</i> , 2009 , 95, 242101	3.4	21
157	Atomic Arrangement at the AlN/Si(110) Interface. <i>Applied Physics Express</i> , 2008 , 1, 061104	2.4	20
156	Epitaxy of GaN LEDs on large substrates: Si or sapphire? 2006 ,		20
155	Influence of excitons and electric fields on the dielectric function of GaN: Theory and experiment. <i>Physical Review B</i> , 2006 , 74,	3.3	20
154	Strains and Stresses in GaN Heteroepitaxy -- Sources and Control. <i>Advances in Solid State Physics</i> , 2004 , 313-326		20
153	Leakage currents and Fermi-level shifts in GaN layers upon iron and carbon-doping. <i>Journal of Applied Physics</i> , 2017 , 122, 025704	2.5	19
152	Strain evaluation in AlInN/GaN Bragg mirrors by in situ curvature measurements and ex situ x-ray grazing incidence and transmission scattering. <i>Applied Physics Letters</i> , 2010 , 97, 181105	3.4	19
151	Low-temperature/high-temperature AlN superlattice buffer layers for high-quality Al _x Ga _{1-x} N on Si (1 1 1). <i>Journal of Crystal Growth</i> , 2009 , 311, 3742-3748	1.6	19
150	Eliminating stacking faults in semi-polar GaN by AlN interlayers. <i>Applied Physics Letters</i> , 2011 , 99, 021905	3.4	19

149	Growth of AlInN/GaN distributed Bragg reflectors with improved interface quality. <i>Journal of Crystal Growth</i> , 2015 , 414, 105-109	1.6	18
148	On reduction of current leakage in GaN by carbon-doping. <i>Applied Physics Letters</i> , 2016 , 109, 212102	3.4	18
147	Heavy Si doping: The key in heteroepitaxial growth of a-plane GaN without basal plane stacking faults?. <i>Physica Status Solidi (B): Basic Research</i> , 2011 , 248, 578-582	1.3	17
146	InAlN/GaN/Si heterostructures and field-effect transistors with lattice matched and tensely or compressively strained InAlN. <i>Applied Physics Letters</i> , 2010 , 97, 173505	3.4	17
145	Metalorganic vapor-phase epitaxy of GaN layers on Si substrates with Si(1 1 0) and other high-index surfaces. <i>Journal of Crystal Growth</i> , 2010 , 312, 180-184	1.6	17
144	Electrical microcharacterization of dislocation-related charges in GaN-based single layers by scanning probe microscopy techniques. <i>Journal of Crystal Growth</i> , 2003 , 248, 542-547	1.6	17
143	Gallium-nitride-based devices on silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 1940-1949		17
142	Time-delayed indium incorporation in ultrathin (In _x Ga _{1-x} N/GaN) multiple quantum wells grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2003 , 82, 4558-4560	3.4	17
141	A low-temperature evaporation route for ZnO nanoneedles and nanosaws. <i>Applied Physics A: Materials Science and Processing</i> , 2005 , 80, 457-460	2.6	17
140	In-situ growth monitoring of AlInN/AlGaIn distributed Bragg reflectors for the UV-spectral range. <i>Journal of Crystal Growth</i> , 2013 , 370, 87-91	1.6	16
139	Ge as a surfactant in metal-organic vapor phase epitaxy growth of a-plane GaN exceeding carrier concentrations of 10 ²⁰ cm ⁻³ . <i>Applied Physics Letters</i> , 2013 , 103, 012103	3.4	16
138	GaN heteroepitaxy on Si(0 0 1). <i>Journal of Crystal Growth</i> , 2004 , 272, 496-499	1.6	16
137	Growth and stacking fault reduction in semi-polar GaN films on planar Si(112) and Si(113). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 507-510		15
136	MOVPE growth of semi-polar GaN light-emitting diode structures on planar Si(112) and Si(113) substrates. <i>Journal of Crystal Growth</i> , 2013 , 370, 288-292	1.6	15
135	Capacitance transient study of the deep Fe acceptor in indium phosphide. <i>Physical Review B</i> , 1997 , 56, 10241-10248	3.3	15
134	Electroreflectance spectroscopy of Pt _{0.5} Al _{0.5} GaN/GaN heterostructures exposed to gaseous hydrogen. <i>Applied Physics Letters</i> , 2006 , 88, 024101	3.4	15
133	Phonons and free-carrier properties of binary, ternary, and quaternary group-III nitride layers measured by Infrared Spectroscopic Ellipsometry. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 1750-1769		15
132	Bright blue to orange photoluminescence emission from high-quality InGaN/GaN multiple-quantum-wells on Si(111) substrates. <i>Applied Physics Letters</i> , 2002 , 81, 1591-1593	3.4	15

131	Breakdown of Far-Field Raman Selection Rules by Light-Plasmon Coupling Demonstrated by Tip-Enhanced Raman Scattering. <i>Journal of Physical Chemistry Letters</i> , 2017 , 8, 5462-5471	6.4	14
130	GaN micromachined FBAR structures for microwave applications. <i>Superlattices and Microstructures</i> , 2006 , 40, 426-431	2.8	14
129	Heteroepitaxy and nitrogen doping of high-quality ZnO. <i>Journal of Crystal Growth</i> , 2004 , 272, 800-804	1.6	14
128	Growth of ZnO Layers by Metal Organic Chemical Vapor Phase Epitaxy. <i>Physica Status Solidi A</i> , 2002 , 192, 189-194		14
127	Thin-film InGaN/GaN Vertical Light Emitting Diodes Using GaN on Silicon-On-Insulator Substrates. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H460		13
126	Direct evidence for selective impurity incorporation at the crystal domain boundaries in epitaxial ZnO layers. <i>Applied Physics Letters</i> , 2004 , 85, 1976-1978	3.4	13
125	Depth-resolving structural analysis of GaN layers by skew angle x-ray diffraction. <i>Applied Physics Letters</i> , 2004 , 84, 3537-3539	3.4	13
124	Simultaneous measurement of wafer curvature and true temperature during metalorganic growth of group-III nitrides on silicon and sapphire. <i>Physica Status Solidi (B): Basic Research</i> , 2005 , 242, 2570-2574	1.3	13
123	Temperature rise in InGaN/GaN vertical light emitting diode on copper transferred from silicon probed by Raman scattering. <i>Journal of Applied Physics</i> , 2010 , 108, 114501	2.5	12
122	Micro-structural anisotropy of a-plane GaN analyzed by high resolution X-ray diffraction. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S498-S501		12
121	Green to blue polarization compensated c-axis oriented multi-quantum wells by AlGaInN barrier layers. <i>Applied Physics Letters</i> , 2013 , 102, 062110	3.4	11
120	Growth and characterization of stacking fault reduced GaN $(1,0,\bar{1},3)$ on sapphire. <i>Journal Physics D: Applied Physics</i> , 2013 , 46, 125308	3	11
119	Microstructure of gallium nitride films grown on silicon (110). <i>Applied Physics Letters</i> , 2010 , 96, 231908	3.4	11
118	AlInN/GaN based multi quantum well structures \square growth and optical properties. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S451-S454		11
117	Growth of Ru doped semi-insulating InP by low pressure metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 1998 , 195, 69-73	1.6	11
116	Crystallographic and electric properties of MOVPE-grown AlGaIn/GaN-based FETs on Si(001) substrates. <i>Journal of Crystal Growth</i> , 2007 , 299, 399-403	1.6	11
115	Surface stability of InGaN-channel based HFETs. <i>Electronics Letters</i> , 2003 , 39, 1614	1.1	11
114	Metalorganic chemical vapor phase epitaxy of narrow-band distributed Bragg reflectors realized by GaN:Ge modulation doping. <i>Journal of Crystal Growth</i> , 2016 , 440, 6-12	1.6	10

113	Anisotropic bow and plastic deformation of GaN on silicon. <i>Journal of Crystal Growth</i> , 2013 , 370, 278-281.	1.6	10
112	Luminescence from two-dimensional electron gases in InAlN/GaN heterostructures with different In content. <i>Applied Physics Letters</i> , 2012 , 100, 212101	3.4	10
111	Influence of anisotropic strain on excitonic transitions in a-plane GaN films. <i>Microelectronics Journal</i> , 2009 , 40, 322-324	1.8	10
110	Local p-type conductivity in n-GaN and n-ZnO layers due to inhomogeneous dopant incorporation. <i>Physica B: Condensed Matter</i> , 2006 , 376-377, 703-706	2.8	10
109	Temperature dependence of the built-in electric field strength of AlGaIn/GaN heterostructures on Si(111) substrate. <i>Superlattices and Microstructures</i> , 2004 , 36, 693-700	2.8	10
108	Deep-level transient-spectroscopy study of rhodium in indium phosphide. <i>Physical Review B</i> , 1996 , 53, 7190-7196	3.3	10
107	Reliable GaN-Based THz Gunn Diodes With Side-Contact and Field-Plate Technologies. <i>IEEE Access</i> , 2020 , 8, 84116-84122	3.5	9
106	Cathodoluminescence of epitaxial GaN and ZnO thin films for scintillator applications. <i>Journal of Crystal Growth</i> , 2009 , 311, 3984-3988	1.6	9
105	MOVPE Growth and Characterization of AlInN FET Structures on Si(111). <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1068, 1		9
104	Metalorganic vapor phase epitaxy of ZnO: towards p-type conductivity 2007 , 6474, 32		9
103	High-resolution x-ray analysis of compressively strained 1.55 nm GaInAs/AlGaInAs multiquantum well structures near the critical thickness. <i>Applied Physics Letters</i> , 1995 , 67, 3325-3327	3.4	9
102	Radiation-induced alloy rearrangement in In _x Ga _{1-x} N. <i>Applied Physics Letters</i> , 2017 , 110, 132104	3.4	8
101	Growth of III/Vs on Silicon 2015 , 1249-1300		8
100	Growth of AlInN/AlGaIn distributed Bragg reflectors for high quality microcavities. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 1253-1258		8
99	Thermal stability of the midgap acceptor rhodium in indium phosphide. <i>Applied Physics Letters</i> , 1995 , 67, 479-481	3.4	8
98	Electrical investigations of AlGaIn/AlN structures for LEDs on Si(111). <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011 , 208, 1597-1599	1.6	7
97	Strain profiling of AlInN/GaN distributed Bragg reflectors using in situ curvature measurements and ex situ X-ray diffraction. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2010 , 528, 58-64	5.3	7
96	Valence band tomography of wurtzite GaN by spectroscopic ellipsometry. <i>Applied Physics Express</i> , 2018 , 11, 101001	2.4	7

95	Wafer curvature, temperature inhomogeneity, plastic deformation and their impact on the properties of GaN on silicon power and opto-electronic structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 397-400		6
94	Impact of AlN seeding layer growth rate in MOVPE growth of semi-polar gallium nitride structures on high index silicon. <i>Physica Status Solidi (B): Basic Research</i> , 2011 , 248, 594-599	1.3	6
93	Characterization of AlGaInN layers using X-ray diffraction and fluorescence. <i>Physica Status Solidi (B): Basic Research</i> , 2011 , 248, 622-626	1.3	6
92	Luminescence Properties of Photonic Crystal InGaN/GaN Light Emitting Layers on Silicon-on-Insulator. <i>Electrochemical and Solid-State Letters</i> , 2010 , 13, H343		6
91	Direct microscopic correlation of crystal orientation and luminescence in spontaneously formed nonpolar and semipolar GaN growth domains. <i>Applied Physics Letters</i> , 2010 , 96, 172102	3.4	6
90	Characterization of defects in undoped non c-plane and high resistance GaN layers dominated by stacking faults. <i>Physica B: Condensed Matter</i> , 2009 , 404, 4922-4924	2.8	6
89	Monitoring glycolytic oscillations using AlGaIn/GaN high electron mobility transistors (HEMTs). <i>Sensors and Actuators B: Chemical</i> , 2010 , 149, 310-313	8.5	6
88	Light extraction from GaN-based LED structures on silicon-on-insulator substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 88-91		6
87	Correlation between macroscopic transport parameters and microscopic electrical properties in GaN. <i>Journal of Applied Physics</i> , 2005 , 97, 043710	2.5	6
86	Novel ways to grow thermally stable semi-insulating InP-based layers. <i>Journal of Crystal Growth</i> , 1994 , 145, 455-461	1.6	6
85	Observation of individual stacking faults in GaN microcrystals by x-ray nanodiffraction. <i>Applied Physics Letters</i> , 2017 , 110, 121905	3.4	5
84	Flexible Modulation of Electronic Band Structures of Wide Band Gap GaN Semiconductors Using Bioinspired, Nonbiological Helical Peptides. <i>Advanced Functional Materials</i> , 2018 , 28, 1704034	15.6	5
83	Electronic excitations stabilized by a degenerate electron gas in semiconductors. <i>Communications Physics</i> , 2018 , 1,	5.4	5
82	Characterization of AlInN/AlN/GaN FET structures using x-ray diffraction, x-ray reflectometry and grazing incidence x-ray fluorescence analysis. <i>Journal Physics D: Applied Physics</i> , 2014 , 47, 355106	3	5
81	Al _x Ga _{1-x} N/GaN heterostructures on a thin silicon-on-insulator substrate for metal-semiconductor-metal photodetectors. <i>Journal Physics D: Applied Physics</i> , 2011 , 44, 365102	3	5
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